

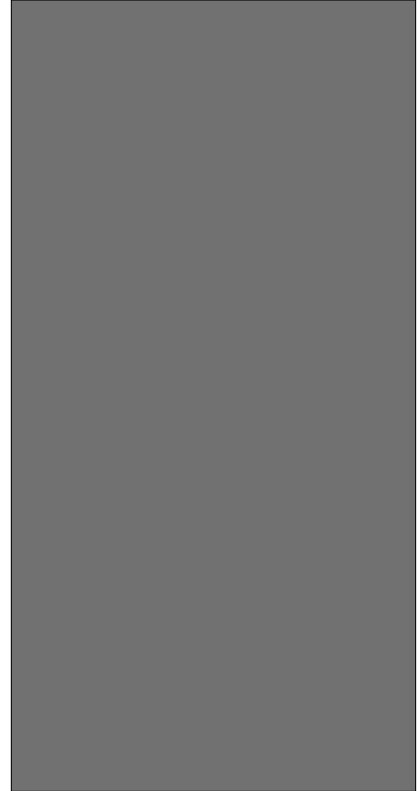


JCT825F 25A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withst





Peak gate current ($t_p=20\mu s$, $T_j=125$)	I_{GM}	5	A
Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	20	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	70	mA
I_H	$I_T=500mA$	-	-	60	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$	1000	-	-	V/ μs
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$	-	2	-	μs
t_{off}		-	50	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=50A$ $t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.72	V
R_D	Dynamic resistance	$T_j=125$	16	m Ω



ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>8</u>	<u>25</u>	<u>F</u>
JieJie Microelectronics Co., Ltd.	SCRs	8: $V_{DRM}/V_{RRM} \bullet 800V$	$I_T(RMS): 25A$	F: TO-220F(Ins)

MARKING

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JCT825F



JieJie Microelectronics Co., Ltd.

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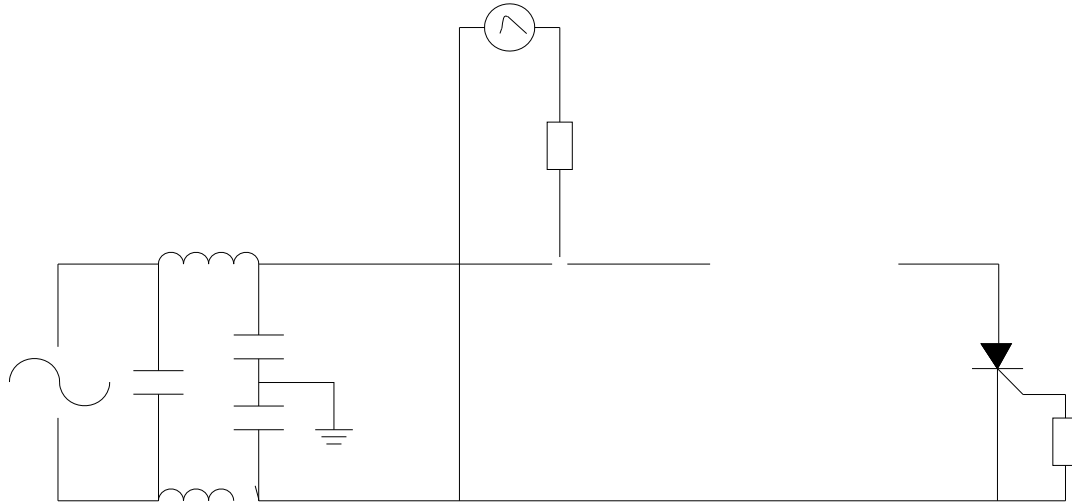
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FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



**ORDERING INFORMATION**

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT825F	800	20	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.13, 2023	A.1.0	Last update
Sept.29, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA



